

Transistors

1.8V Drive Nch MOSFET

RUF015N02

●Structure

Silicon N-channel MOSFET

●Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (1.8V drive).

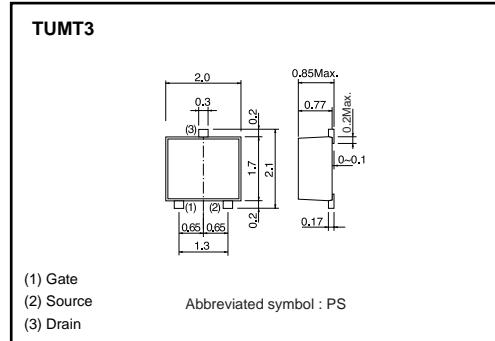
●Applications

Switching

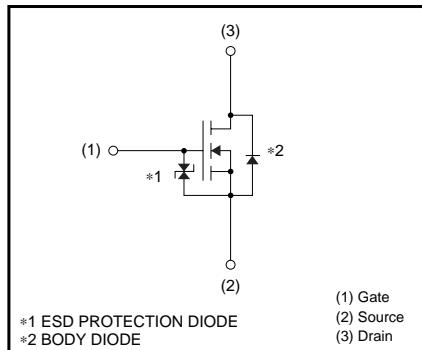
●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RUF015N02		○

●Dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	20	V
Gate-source voltage	V _{GSS}	10	V
Drain current	Continuous	I _D	A
	Pulsed	I _{DP} *1	A
Source current (Body diode)	Continuous	I _S	A
	Pulsed	I _{SP} *1	A
Total power dissipation	P _D *2	0.8	W
Channel temperature	T _{ch}	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

*1 P_{WS}≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	R _{th(ch-a)} *	156	°C/W

* Mounted on a ceramic board

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	—	—	10	μA	V _{GS} =10V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	20	—	—	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 20V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	—	1.0	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	R _{DS (on)*}	—	130	180	mΩ	I _D = 1.5A, V _{GS} = 4.5V
		—	170	240	mΩ	I _D = 1.5A, V _{GS} = 2.5V
		—	220	310	mΩ	I _D = 0.8A, V _{GS} = 1.8V
Forward transfer admittance	Y _{fs} *	1.6	—	—	S	V _{DS} = 10V, I _D = 1.5A
Input capacitance	C _{iss}	—	110	—	pF	V _{DS} = 10V
Output capacitance	C _{oss}	—	18	—	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	—	15	—	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	—	5	—	ns	I _D = 1.0A V _{DD} = 10V
Rise time	t _r *	—	5	—	ns	V _{GS} = 4.5V
Turn-off delay time	t _{d (off)} *	—	20	—	ns	R _L =10Ω
Fall time	t _f *	—	3	—	ns	R _G =10Ω
Total gate charge	Q _g *	—	1.8	2.5	nC	V _{DD} = 10V
Gate-source charge	Q _{gs} *	—	0.3	—	nC	V _{GS} = 4.5V
Gate-drain charge	Q _{gd} *	—	0.3	—	nC	I _D = 1.5A

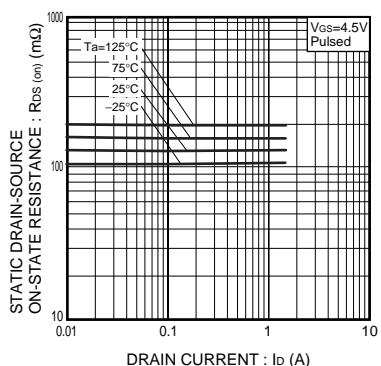
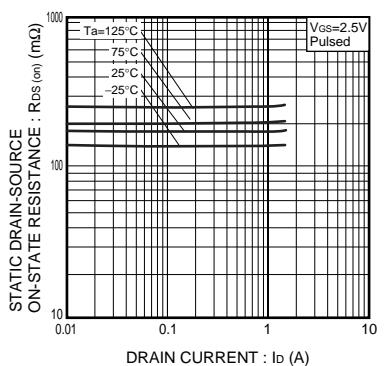
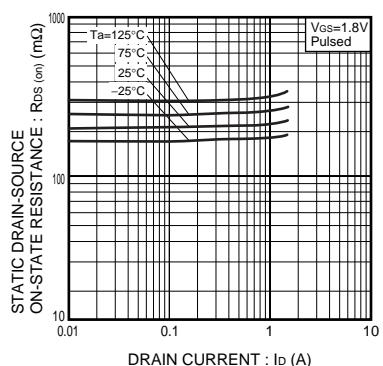
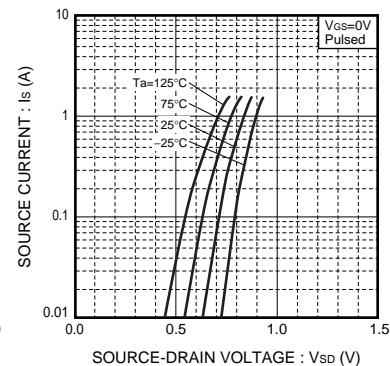
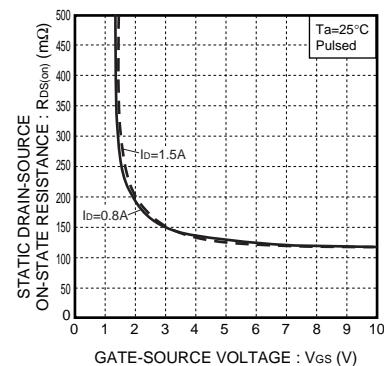
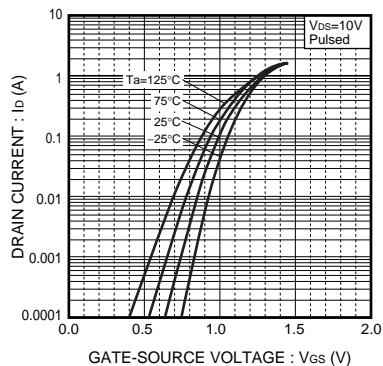
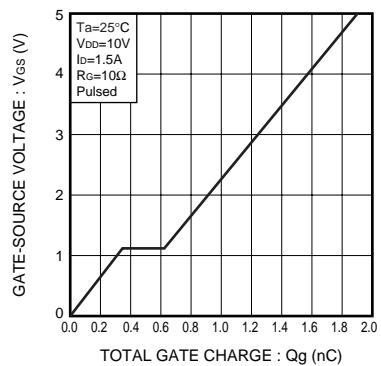
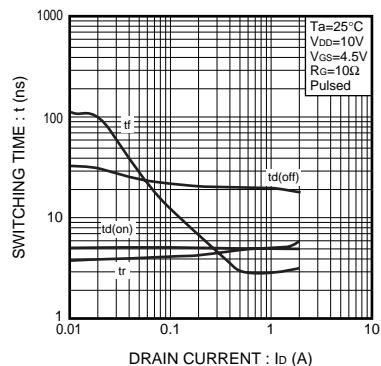
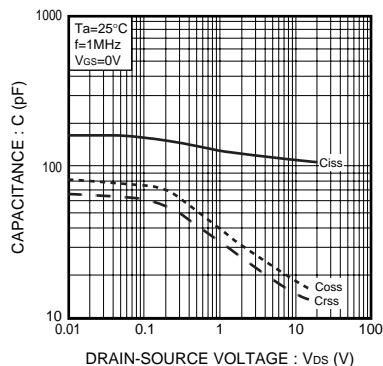
*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	—	—	1.2	V	I _S = 0.6A, V _{GS} =0V

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●Electrical characteristics curves



●Notice

This product might cause chip aging and breakdown under the large electrified environment.
Please consider to design ESD protection circuit.

Appendix

Notes

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